

SNOSAP1A-OCTOBER 2010-REVISED MARCH 2013

LM10QML Operational Amplifier and Voltage Reference

Check for Samples: LM10QML

FEATURES

- Input Offset Voltage: 2.0 mV (max)
- Input Offset Current: 0.7 nA (max)
- Input Bias Current: 20 nA (max)
- Reference Regulation: 0.1% (max)
- Offset Voltage Drift: 2µV/°C
- Reference Drift: 0.002%/°C

DESCRIPTION

The LM10 is a monolithic linear IC consisting of a precision reference, an adjustable reference buffer and an independent, high quality op amp.

The unit can operate from a total supply voltage as low as 1.1V or as high as 40V, drawing only 270 μ A. A complementary output stage swings within 15 mV of the supply terminals or will deliver ±20 mA output current with ±0.4V saturation. Reference output can be as low as 200 mV.

The circuit is recommended for portable equipment and is completely specified for operation from a single power cell. In contrast, high output-drive capability, both voltage and current, along with thermal overload protection, suggest it in demanding general-purpose applications.

The device is capable of operating in a floating mode, independent of fixed supplies. It can function as a remote comparator, signal conditioner, SCR controller or transmitter for analog signals, delivering the processed signal on the same line used to supply power. It is also suited for operation in a wide range of voltage- and current-regulator applications, from low voltages to several hundred volts, providing greater precision than existing ICs.

Connection and Functional Diagram



Package Number NEV0008A

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Figure 2. Operational Amplifier Schematic — (Pin numbers are for 8-pin packages)





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



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Absolute Maximum Ratings⁽¹⁾

Total Supply Voltage	45V		
Differential Input Voltage (2)	±40V		
Power Dissipation (P _{Dmax}) ⁽³⁾	Internally Limited		
Output Short-circuit Duration (4)	Continuous		
Storage Temperature Range	−55°C ≤ T _A ≤ +150°C		
Maximum Junction Temperature (150°C		
Lead Temperature (Soldering 10) seconds)		300°C
Thermal Resistance	θ_{JA}	Still Air	150°C
		500LF/Min Air flow	45°C
	θ_{JC}	45°C	
ESD			Rating to be determined

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not ensure specific performance limits. For ensured specifications and test conditions, see the Electrical Characteristics. The ensured specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

(2) The Input voltage can exceed the supply voltages provided that the voltage from the input to any other terminal does not exceed the maximum differential input voltage and excess dissipation is accounted for when V_I< V_S⁻.

(3) The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{Jmax} (maximum junction temperature), θ_{JA} (package junction to ambient thermal resistance), and T_A (ambient temperature). The maximum allowable power dissipation at any temperature is P_{Dmax} = (T_{Jmax} - T_A)/θ_{JA} or the number given in the Absolute Maximum Ratings, whichever is lower.

(4) Internal thermal limiting prevents excessive heating that could result in sudden failure, but the IC can be subjected to accelerated stress with a shorted output and worst-case conditions.

Quality Conformance Inspection

Mil-Std-883, Method 5005 - Group A

Subgroup	Description	Temp °C
1	Static tests at	+25
2	Static tests at	+125
3	Static tests at	-55
4	Dynamic tests at	+25
5	Dynamic tests at	+125
6	Dynamic tests at	-55
7	Functional tests at	+25
8A	Functional tests at	+125
8B	Functional tests at	-55
9	Switching tests at	+25
10	Switching tests at	+125
11	Switching tests at	-55
12	Settling time at	+25
13	Settling time at	+125
14	Settling time at	-55

EXAS STRUMENTS

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LM10H Electrical Characteristics DC Parameters

The following conditions apply to all the following parameters, unless otherwise specified.

DC: At room temperature $1.2V \le V_S \le 45V$, $V_S \le V_{CM} \le V \pm 0.85V$. DC: At temperature extremes $1.3V \le V_S \le 45V$, $V_S \le V_{CM} \le V \pm 1.0V$.

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub- groups
				-2.0	2.0	mV	1
V _{IO}		$I_{O} = 0 \Pi A$		-3.0	3.0	mV	2, 3
	Input Offert Voltage	$V_{S} = 1.2V, I_{O} = \pm 2mA$		-3.0	3.0	mV	1
	input Onset voltage	$V_S = 1.3V$, $I_O = \pm 2mA$		-4.0	4.0	mV	2, 3
		$V_S = 4V, I_O = \pm 20mA$		-3.0	3.0	mV	1
		$V_{S} = 4V, I_{O} = \pm 15mA$		-4.0	4.0	mV	2, 3
lio	Input Offset Current			-0.7	0.7	nA	1
0				-1.5	1.5	nA	2, 3
lun	Input Bias Current				20	nA	1
IB	input bias ourient				30	nA	2, 3
CMRR	Common Mode Rejection	$V_{0} = 45V_{0} = 20V_{0} \le V_{0} \le 24.2V_{0}$		93		dB	1
OWIN		VS - 43V, 20V - VCM - 24.2V		87		dB	2, 3
		V _S ⁺ = 0.85V, -0.35V ≥ V _S ⁻ ≥ -44.2V		90		dB	1
DCDD	Supply Voltage Rejection	V _S ⁺ = 1V, -0.3V ≥ V _S ⁻ ≥ -44.2V		84		dB	2, 3
FORK	Supply vollage Rejection	$0.85V \le V_{S}^{+} \le 44.6V,$ $V_{S}^{-} = -0.35V$		96		dB	1
		$1V \le V_{S}^{+} \le 44.6V, V_{S}^{-} = -0.3V$		90		dB	2, 3
V _{RLine}	Line Regulation	L _ 1mA		91		dB	1
	Line Regulation I _{Ref} = 1mA			85		dB	2, 3
V	Lood Pogulation	$V_{S} = 1.2V, 0 \le I_{O} \le 1mA$		60		dB	1
V RLoad		$V_{S} = 1.3V, 0 \le I_{O} \le 1mA$		57		dB	2, 3
1-	Supply Current				400	μA	1
is					500	μA	2, 3
		$V_{\rm S} = \pm 20 V, I_{\rm O} = 0 A,$		120		К	4
V _{RLine} V _{RLoad} I _S		$V_0 = \pm 19.95V$		80		K	5, 6
		$V_S = \pm 2V$, $I_O = \pm 20mA$, $V_O = \pm 1.4V$		5.0		К	4
Av	Large Signal Voltage Gain	$V_S = \pm 2V$, $I_O = \pm 15$ mA, $V_O = \pm 1.4V$		1.5		К	5, 6
		$ \begin{array}{l} {\sf V_S}^+ = 0.85{\sf V}, {\sf V_{CM}} = -0.25{\sf V} \\ {\sf V_S}^- = -0.35{\sf V}, {\sf I_O} = \pm 2{\sf mA}, \\ -0.15{\sf V} \le {\sf V_O} \le 0.65{\sf V}, \end{array} $		1.5		к	4
		$ \begin{array}{l} {V_{\rm{S}}}^+ = 1V, V_{\rm{CM}} = -0.35V \\ {V_{\rm{S}}}^- = -0.3V, I_{\rm{O}} = \pm 2m{\rm{A}}, \\ +0.05V \le V_{\rm{O}} \le 0.65V, \end{array} $		0.5		К	5, 6
		$1.1V \le V_{OUT} \le 6.1V$, -5mA $\le I_{OUT} \le -0.1mA$	See ⁽¹⁾	14		к	4
A	Shunt Coin	$1.2V \le V_{OUT} \le 6.2V$, -5mA $\le I_{OUT} \le -0.1mA$	See ⁽¹⁾	6.0		к	5, 6
∽VSH		$1.4V \le V_{OUT} \le 6.4V$, -5mA $\le I_{OUT} \le -0.1mA$	See ⁽¹⁾	8.0		к	4
PSRR V _{RLine} V _{RLoad} Is A _V		$1.4V \le V_{OUT} \le 6.4V$, -20mA $\le I_{OUT} \le -0.1$ mA	See ⁽¹⁾	4.0		к	5, 6

(1) This defines operation in floating applications such as the bootstrapped regulator or two-wire transmitter. Output is connected to the V_S^+ terminal of the IC and input common mode is referred to V_S (see Typical Applications -). Effect of larger output-voltage swings with higher load resistance can be accounted for by adding the positive-supply rejection error.



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LM10H Electrical Characteristics DC Parameters (continued)

The following conditions apply to all the following parameters, unless otherwise specified. DC: At room temperature $1.2V \le V_S \le 45V$, $V_S \le V_{CM} \le V \pm 0.85V$. DC: At temperature extremes $1.3V \le V_S \le 45V$, $V_S \le V_{CM} \le V \pm 1.0V$.

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub- groups
	Amplifier Coin	$0.2V \le V_{Ref} \le 35V$, $I_{Ref} = 1mA$		50		К	
Av	Ampiller Gain			23		К	
M	Foodbook Conce Vieltoge	$0.2V \le V_{\text{Ref}} \le 35V,$		195	205	mV	
VSense	Feedback Sense voltage	0 ≤ I _{Ref} ≤ 1 mA		194	206	mV	
					50	nA	
Sense	Feedback Current				65	nA	
A 1	Sumahu Current Channe	$0.5V \le V_0 \le 25V$		-75	75	μA	
ΔI _S	Supply Current Change	$V_{\rm S} = 5V, 4.5V \le V_{\rm O} \le 5V$		-60	60	μA	
RI			See (2)		250	KΩ	
	Input Resistance		See (2)		150	KΩ	

(2) Specified parameter, not tested,



Definition of Terms

- Input offset voltage: That voltage which must be applied between the input terminals to bias the unloaded output in the linear region.
- **Input offset current:** The difference in the currents at the input terminals when the unloaded output is in the linear region.
- Input bias current: The absolute value of the average of the two input currents.
- **Input resistance:** The ratio of the change in input voltage to the change in input current on either input with the other grounded.
- Large signal voltage gain: The ratio of the specified output voltage swing to the change in differential input voltage required to produce it.
- **Shunt gain:** The ratio of the specified output voltage swing to the change in differential input voltage required to produce it with the output tied to the V_S^+ terminal of the IC. The load and power source are connected between the V_S^+ and V_S^- terminals, and input common-mode is referred to the V_S^- terminal.
- **Common-mode rejection:** The ratio of the input voltage range to the change in offset voltage between the extremes.
- **Supply-voltage rejection:** The ratio of the specified supply-voltage change to the change in offset voltage between the extremes.
- Line regulation: The average change in reference output voltage over the specified supply voltage range.
- Load regulation: The change in reference output voltage from no load to that load specified.
- **Feedback sense voltage:** The voltage, referred to V_S, on the reference feedback terminal while operating in regulation.
- **Reference amplifier gain:** The ratio of the specified reference output change to the change in feedback sense voltage required to produce it.
- Feedback current: The absolute value of the current at the feedback terminal when operating in regulation.
- **Supply current:** The current required from the power source to operate the amplifier and reference with their outputs unloaded and operating in the linear range.





Typical Performance Characteristics (Op Amp)





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-0.2

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Figure 22.













OFFSET VOLTAGE CHANGE (mV)



5 m A

, T_ = 25॑°C

_{OUT} = 5 mÅ

-55°C

ουτ

7

. Г. = 125°С

Vol

8

Shunt Gain

I_{OUT} = 0.1 mA

5 6 7 8

OUTPUT VOLTAGE (V)

Figure 29.

Shunt Gain

3

20 m A

3

4

OUTPUT VOLTAGE (V)

Figure 31.

Shunt Gain

mi

3 4 5 6 7 8

OUTPUT VOLTAGE (V)

Figure 33.

5 6



REFERENCE CHANGE (%)

1k

100

10

REFERENCE NOISE (nV/\/Hz)

SATURATION VOLTAGE (V)

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6

100 125

10

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Typical Applications

Circuit descriptions available in application note AN-211 (SNOA638).

(Pin numbers are for devices in 8-pin packages)

Op Amp Offset Adjustment





Limited Range With Boosted Reference

Positive Regulators

Use only electrolytic output capacitors.

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LM10QML

= 50V

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Laboratory Power Supply



*V_O=10⁻⁴ R3

HV Regulator



 $V_{OUT} = \frac{R2}{R1} V_{REF}$

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*800°C Threshold Is Established By Connecting Balance To V_{Ref}.



Remote Amplifier



*Provides Hysteresis



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Transmitter for Bridge Sensor



Precision Thermocouple Transmitter



10 mA \leq I_{OUT} \leq 50 mA ~ 500°C \leq T_P \leq 1500°C ~ *Gain Trim

Resistance Thermometer Transmitter



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Optical Pyrometer



++Level-shift Trim*Scale Factor Trim+Copper Wire Wound

 $1 \text{ mA} \le I_{OUT} \le 5 \text{ mA}$ $0.01 \le \frac{I_{D2}}{I_{D1}} \le 100$



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Thermocouple Transmitter



200°C≤T_p≤700°C 1 mA≤I_{OUT}≤5 mA †Gain Trim

Logarithmic Light Sensor



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Single-cell Voltage Monitor



Battery-threshold Indicator $V_{TH} = 6V$ $V_{TH} = 100$ $V_{TH} = 1000$ $V_{TH} = 1000$ $V_{TH} =$

Double-ended Voltage Monitor



Flash Rate Increases Above 6V and Below 15V

Flashes Above 1.2V Rate Increases With Voltage



Input 10 mV, 100nA Full-Scale

20 Submit Documentation Feedback



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*Trim For Span †Trim For Zero



 $1 \leq \lambda/\lambda_0 \leq 10^5$



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Microphone Amplifier



 $\begin{array}{l} Z_{OUT}{\sim}680\Omega @ 5 \text{ kHz} \\ A_V \leq 1 \text{k} \\ f_1{\sim}100 \text{ Hz} \\ f_2{\sim}5 \text{ kHz} \\ R_L{\sim}500 \\ *Max \text{ Gain Trim} \end{array}$



†Controls "Loop Gain"*Optional Frequency Shaping



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Circuit descriptions available in application note AN-211 (SNOA638).

APPLICATION HINTS

With heavy amplifier loading to V_{S} , resistance drops in the V_{S} lead can adversely affect reference regulation. Lead resistance can approach 1Ω . Therefore, the common to the reference circuitry should be connected as close as possible to the package.

TEXAS INSTRUMENTS

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Table 1. Revision History

Date Released	Revision	Section	Changes
10/26/2010	A	New release to corporate format	1 MDS converted to standard corporate format. MNLM10-X Rev 0AL will be archived
03/26/2013	А	All sections	Changed layout of National Data Sheet to TI format



PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	. ,						(6)	.,			
5962-8760401GA	ACTIVE	TO-CAN	LMG	8	20	RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125	(LM10H/883, LM158H) 5962-8760401GA Q A CO 5962-8760401GA Q > T	Samples
LM10H/883	ACTIVE	TO-CAN	LMG	8	20	RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125	(LM10H/883, LM158H) 5962-8760401GA Q A CO 5962-8760401GA Q > T	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



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PACKAGE MATERIALS INFORMATION

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TRAY



Chamfer on Tray corner indicates Pin 1 orientation of packed units.

*All dimensions are not	minal

Device	Package Name	Package Type	Pins	SPQ	Unit array matrix	Max temperature (°C)	L (mm)	W (mm)	K0 (µm)	P1 (mm)	CL (mm)	CW (mm)
5962-8760401GA	LMG	TO-CAN	8	20	2 X 10	150	126.49	61.98	8890	11.18	12.95	18.54
LM10H/883	LMG	TO-CAN	8	20	2 X 10	150	126.49	61.98	8890	11.18	12.95	18.54

LMG0008A

PACKAGE OUTLINE

TO-CAN - 5.72 mm max height

METAL CYLINDRICAL PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters [inches]. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.



LMG0008A

EXAMPLE BOARD LAYOUT

TO-CAN - 5.72 mm max height

METAL CYLINDRICAL PACKAGE





	REVISIONS									
REV	DESCRIPTION	ECR	DATE	ENGINEER / DRAFTER						
А	RELEASE NEW DRAWING	2174627	07/10/2018	V. DASIKA / K. SINCERBOX						
В	CHANGE TO DUAL DIMENSIONING MM [INCH] FORMAT	2175848	08/17/2018	V. DASIKA / K. SINCERBOX						

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